March 2000



FDP5645/FDB5645 60V N-Channel PowerTrench® MOSFET

General Description

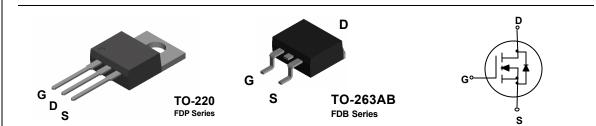
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 80 A, 60 V. $R_{\rm DS(ON)} = 0.0095 \ \Omega \ @ V_{\rm GS} = 10 \ V$ $R_{DS(ON)} = 0.011 \ \Omega @ V_{GS} = 6 \ V.$
- · Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low R_{DS(ON)}.
- 175°C maximum junction temperature rating.



Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter	FDP5645 FDB5645	Units
V _{DSS}	Drain-Source Voltage	60	V
V _{GSS}	Gate-Source Voltage	±20	V
l _D	Maximum Drain Current – Continuous (note 3)	80	Α
	– Pulsed	300	
PD	Total Power Dissipation @ $T_c = 25^{\circ}C$	125	W
	Derate above 25°C	0.83	W/°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-65 to +175	°C
TL	Maximum lead termperature for soldering purposes, 1/8" from case for 5 seconds	+275	°C
Therma	I Characteristics		
R _{0JC}	Thermal Resistance, Junction-to-Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

 $R_{\theta JA}$ Thermal Resistance, Junction-to-Ambient

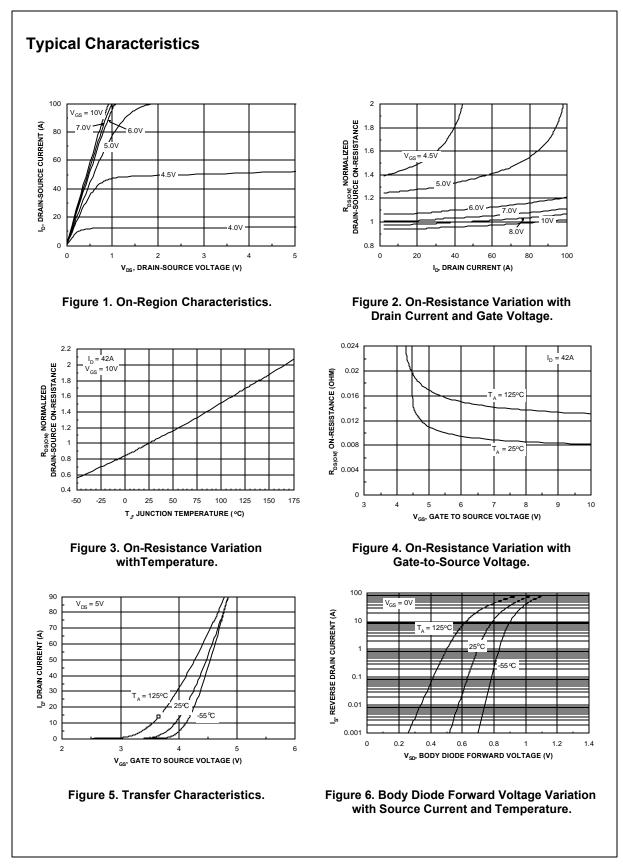
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB5645	FDB5645	13"	24mm	800 units
FDP5645	FDP5645	note 2		

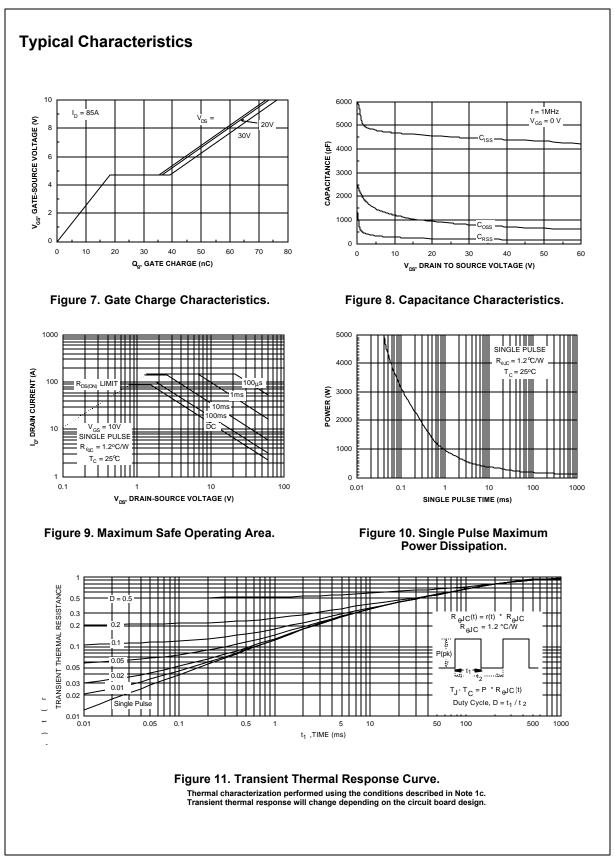
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-So	burce Avalanche Ratings (Note ?	1)				
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 40 \text{ V}, I_D = 80 \text{ A}$			800	mJ
lar	Maximum Drain-Source Avalanche Current				80	A
Off Chai	racteristics					
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V$, $I_D = 250 \mu A$	60	[V
<u>ΔBV dss</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		64		mV/ºC
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 48 V$, $V_{GS} = 0 V$			1	μΑ
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate–Body Leakage, Reverse	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			-100	nA
	acteristics (Note 1)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	-	4	V
<u>ΔVgs(th</u>) ΔTj	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		-7.8		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{array}{ c c c c c c c c } V_{GS} = 10 \ V, & l_D = 40 \ A \\ V_{GS} = 10 V, & l_D = 40 \ A, \ T_J = 125^\circ C \\ V_{GS} = 6 \ V, & l_D = 38 \ A \end{array}$		8 13 9	9.5 18 11	mΩ
D(on)	On–State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	60			Α
g fs	Forward Transconductance	$V_{DS} = 5 V$, $I_D = 40 A$		88		S
Dynamio	Characteristics	•				
Ciss	Input Capacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		4468	1	pF
	Output Capacitance			810		pF
C _{rss}	Reverse Transfer Capacitance			198		pF
	ng Characteristics (Note 2)					μ.
t _{d(on)}	Turn–On Delay Time	$V_{DD} = 30 V$, $I_D = 1 A$,		21	30	ns
t _r	Turn-On Rise Time	$V_{GS} = 30 V$, $I_D = 1 A$, $V_{GS} = 10 V$, $R_{GEN} = 6 \Omega$		13	20	ns
t _{d(off)}	Turn-Off Delay Time			77	90	ns
t _f	Turn–Off Fall Time	_		42	50	ns
Qg	Total Gate Charge	$V_{DS} = 30 \text{ V}.$ $l_D = 80 \text{ A}.$		76	107	nC
Q _{gs}	Gate-Source Charge	$V_{DS} = 30 V$, $I_D = 80 A$, $V_{GS} = 10 V$		18	107	nC
	5	-		21		
Q _{gd}	Gate–Drain Charge			21		nC
Drain-S	ource Diode Characteristics					
ls I-	Maximum Continuous Drain-Source			l T	80	A
	Drain–Source Diode Forward	$V_{GS} = 0 V$, $I_S = 40 A$		0.9	1.3	V
Is V _{SD} otes: Pulse Test: Pu	Maximum Pulsed Drain-Source Dioc	le Forward Current		0.9	300	

FDP5645/FDB5645

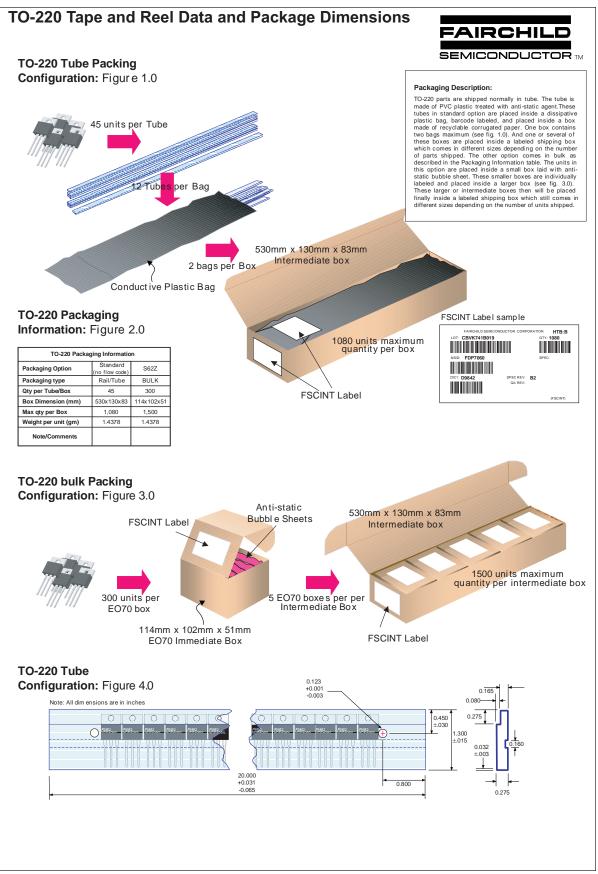


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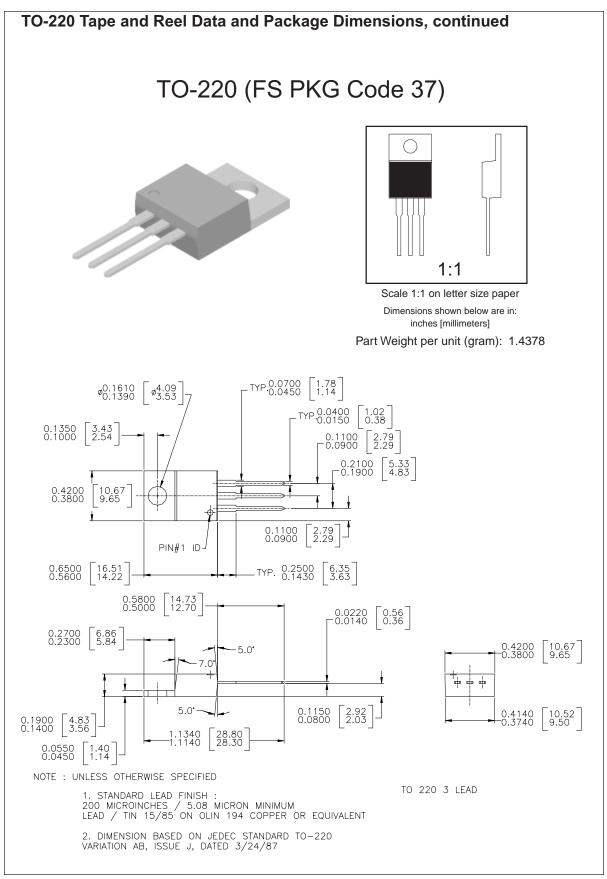


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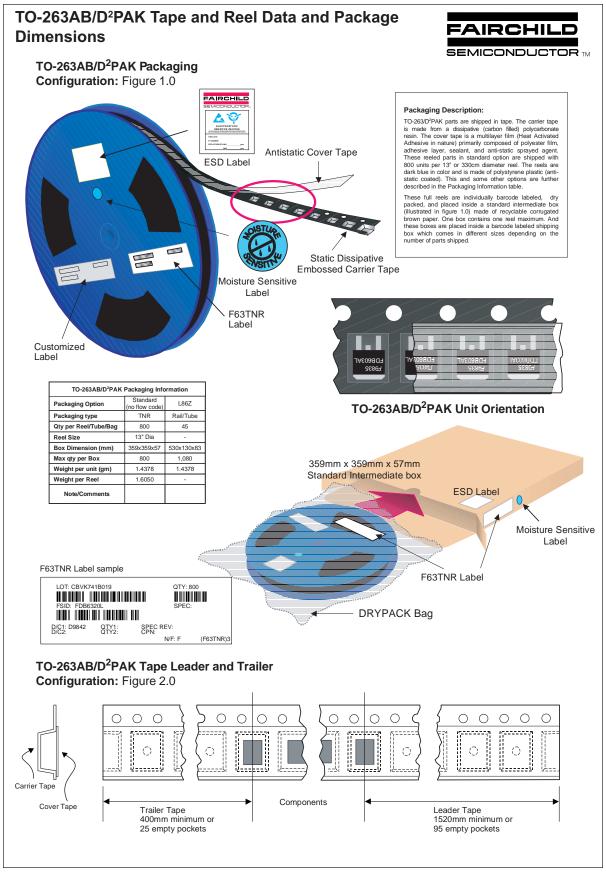
FDP5645/FDB5645 Rev. B (W)



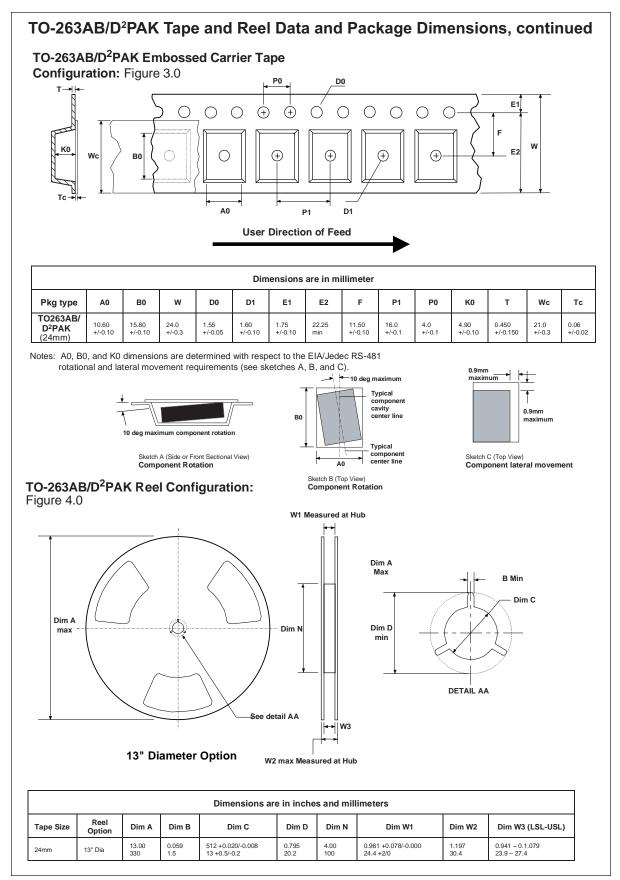
August 1999, Rev. B

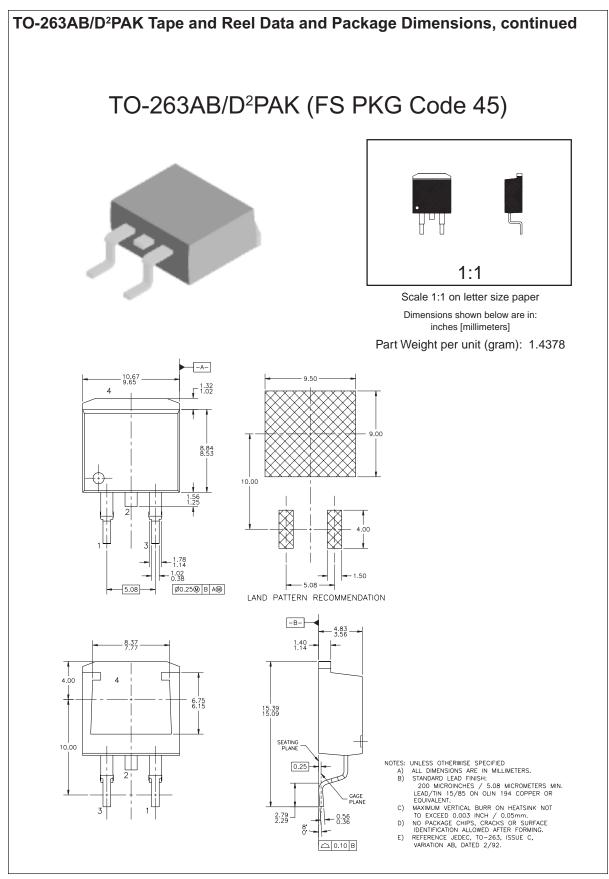


September 1998, Rev. A



September 1999, Rev. B





August 1998, Rev. A

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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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